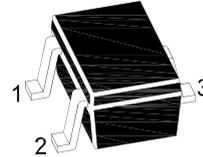


NPN Silicon Epitaxial Transistor

for switching and amplifier applications



1.Base 2.Emitter 3.Collector
SOT-523 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

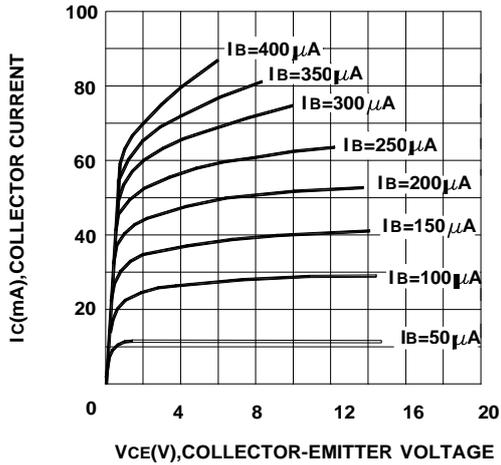
Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	BC846E 80	V
		BC847E, BC850E 50	
		BC848E, BC849E 30	
Collector Emitter Voltage	V_{CEO}	BC846E 65	V
		BC847E, BC850E 45	
		BC848E, BC849E 30	
Emitter Base Voltage	V_{EBO}	BC846E, BC847E 6	V
		BC848E, BC849E, BC850E 5	
Collector Current	I_C	100	mA
Peak Collector Current	I_{CM}	200	mA
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

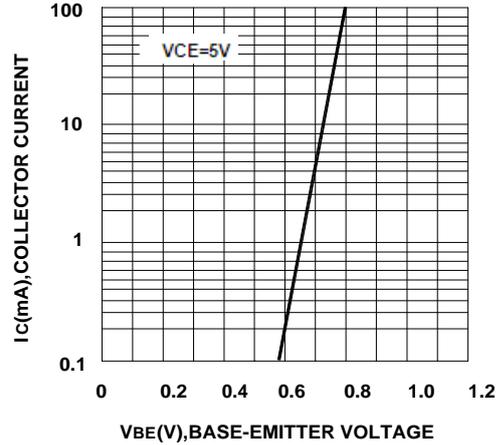
Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ mA}$	Current Gain Group A B C	h_{FE}	110	-	220	-
		h_{FE}	200	-	450	-
		h_{FE}	420	-	800	-
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	I_{CBO}	-	-	15	nA	
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ at $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	$V_{CE(sat)}$	-	-	250	mV	
	$V_{CE(sat)}$	-	-	600	mV	
Base Emitter On Voltage at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ mA}$ at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$	$V_{BE(on)}$	-	-	700	mV	
	$V_{BE(on)}$	-	-	720	mV	
Transition Frequency at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	300	-	MHz	
Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	-	6	pF	

BC846E...BC850E

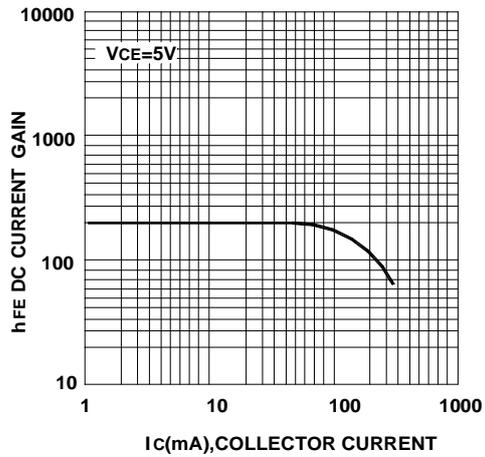
STATIC CHARACTERISTIC



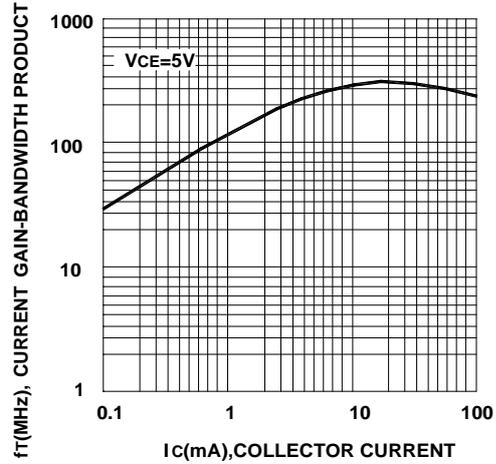
BASE-EMITTER ON VOLTAGE



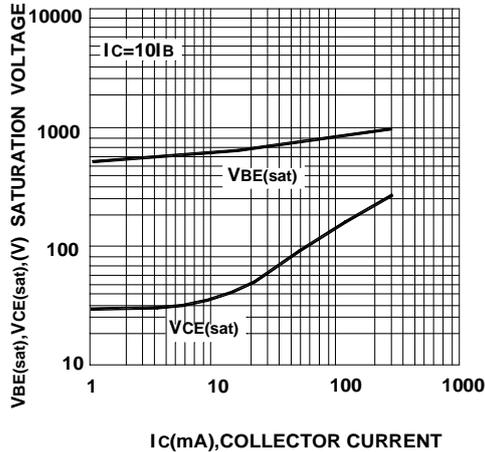
DC CURRENT GAIN



CURRENT GAIN BANDWIDTH PRODUCT



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE

